

### AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended): A method of fabricating  
a ~~low temperature polysilicon (LTPS)~~ thin film  
5 transistor (TFT), ~~the method comprising following~~  
~~steps:~~

providing a substrate;  
forming a polysilicon film on the substrate, the  
polysilicon film defined with a source region,  
10 a drain region, and a channel region between the  
source region and the drain region;  
forming a gate insulating layer ~~on~~ above the  
substrate;  
forming a gate ~~on~~ above the substrate;  
15 performing an ion implantation process to form a  
source in the source region and a drain in the  
drain region;  
forming a silane based silicon nitride layer  
covering the gate and the polysilicon film; and  
20 forming a TEOS based silicon oxide layer on the  
silicon nitride layer.

Claim 2 (currently amended): The method of claim 1  
further comprising following steps:  
25 performing a photo-etching process to form a  
contact hole on the source and ~~another contact~~  
~~hole on the drain~~ respectively; and  
filling a conductive layer in the contact holes,  
the conductive layer being electrically  
30 connected to the source and the drain.

Claim 3 (original): The method of claim 1 wherein the

method of forming the polysilicon film comprises  
following steps:

- forming an amorphous silicon film on the substrate;
- and
- 5 performing an excimer laser annealing process to  
make the amorphous silicon film crystallize to  
the polysilicon film.

Claim 4 (cancelled)

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Claim 5 (original): The method of claim 4 wherein the  
silicon nitride layer comprises 20% to 40% hydrogen  
atoms and serves as a hydrogen source of a  
hydrogenating process.

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Claim 6 (original): The method of claim 1 wherein the  
gate is a metal gate.

Claim 7 (currently amended): The method of claim 1  
20 wherein the silicon oxide has a thickness in a range  
of ~~2500~~500 to 10000 angstroms.

Claim 8 (currently amended): The method of claim 1  
wherein the silicon nitride has a thickness in a range  
25 of 500 to ~~3500~~5000 angstroms.

Claim 9 (original): The method of claim 1 wherein the  
method forms the silicon nitride layer by performing  
a first plasma enhanced chemical vapor deposition  
30 (PECVD) process.

Claim 10 (original): The method of claim 9 wherein the

method forms the silicon oxide layer by performing a second plasma enhanced chemical vapor deposition process.

5 Claim 11 (currently amended): The method of claim 10 wherein the first PECVD process and the second PECVD process are performed in the same ~~reacting~~ chamber.

10 Claim 12 (currently amended): The method of claim 10 wherein the first PECVD process and the second PECVD process are performed in different ~~reacting~~ chambers.

15 Claim 13 (original): The method of claim 1 wherein the low temperature polysilicon thin film transistor is a top gate low temperature polysilicon thin film transistor or a bottom gate low temperature polysilicon thin film transistor.